UNIKC Semiconductor

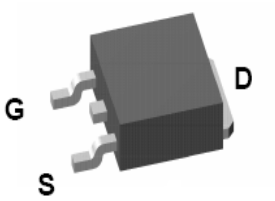
RoHS Compliant

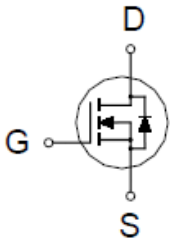
PD548BA

N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	4.6mΩ @V_{GS} = 10V	85A





TO-252

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[2]	T_C = 25 °C	I_D	85	A
	T_C = 100 °C		54	
Pulsed Drain Current[1]		I_{DM}	170	
Avalanche Current		I_{AS}	38	
Avalanche Energy	L =0.1mH	E_{AS}	72	mJ
Power Dissipation	T_C = 25 °C	P_D	59	W
	T_C = 100 °C		23	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.1	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.

[2]Calculated continuous current based on maximum allowable junction temperature, Package limitation current is 40A.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMIT			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.5	1.75	2.35	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V, T_J = 125 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 15A		4.5	7.2	mΩ
		V_{GS} = 10V , I_D = 20A		3.8	4.6	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		70		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		2320		pF
Output Capacitance	C_{oss}			346		
Reverse Transfer Capacitance	C_{rss}			285		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		0.9		Ω
Total Gate Charge[2]	Q_g	V_{DS} =15V, V_{GS} = 10V, I_D = 20A		54		nC
Gate-Source Charge[2]	Q_{gs}			7.5		
Gate-Drain Charge[2]	Q_{gd}			17.3		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 15V, I_D ≅ 20A, V_{GS} = 10V, R_{GEN} = 6Ω		24		nS
Rise Time[2]	t_r			16		
Turn-Off Delay Time[2]	$t_{d(off)}$			63		
Fall Time[2]	t_f			24		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				85	A
Forward Voltage[1]	V_{SD}	I_F = 20A, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = 20A, dI_F/dt = 100A / μS		23		nS
Reverse Recovery Charge	Q_{rr}			10		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3] Calculated continuous current based on maximum allowable junction temperature, Package limitation current is 40A.

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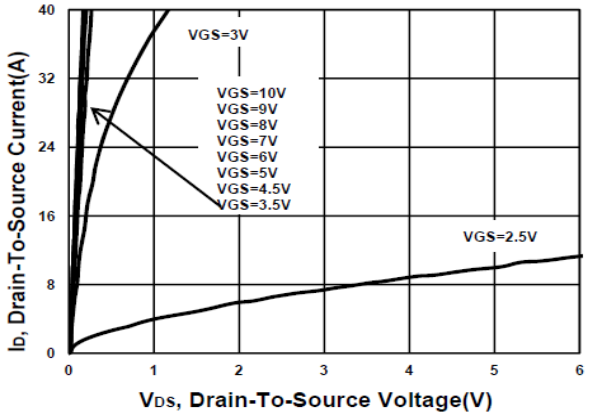
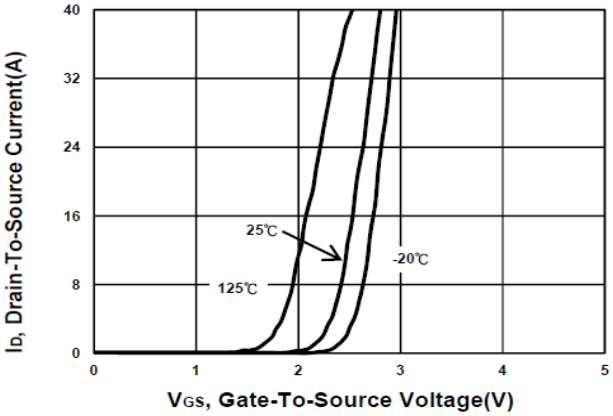
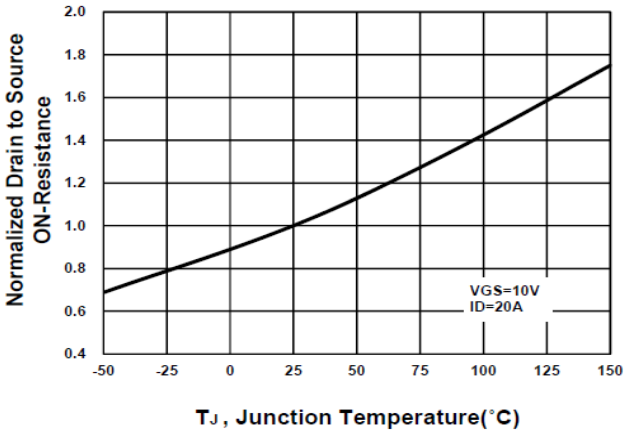
Output Characteristics



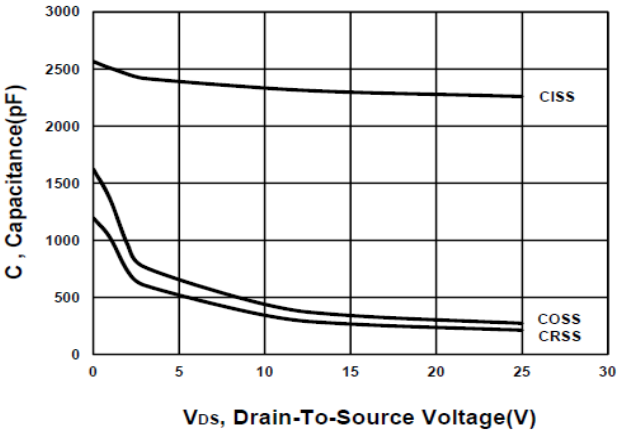
Transfer Characteristics



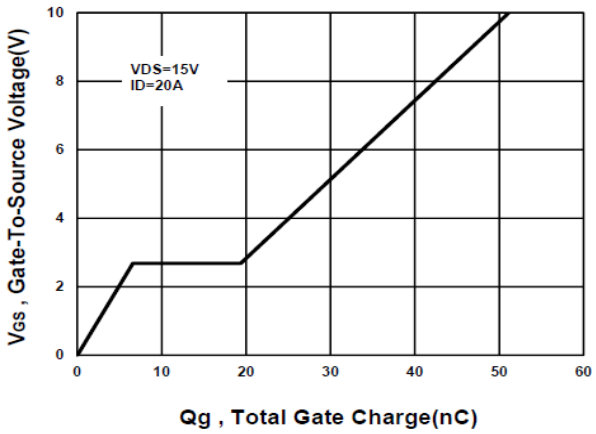
On-Resistance VS Temperature



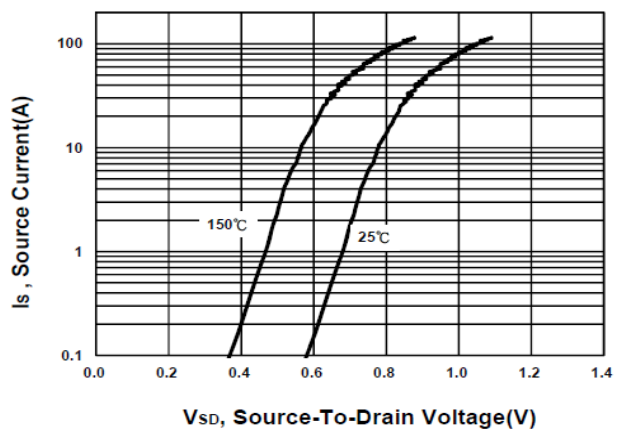
Capacitance Characteristic



Gate charge Characteristics



Source-Drain Diode Forward Voltage



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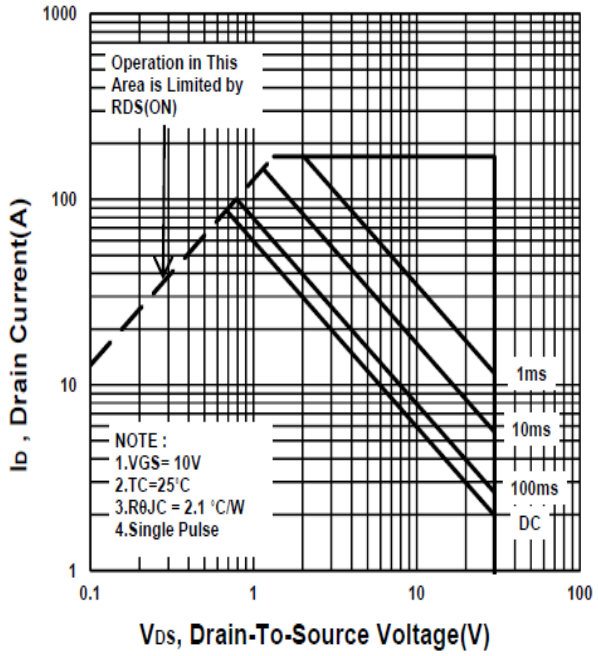
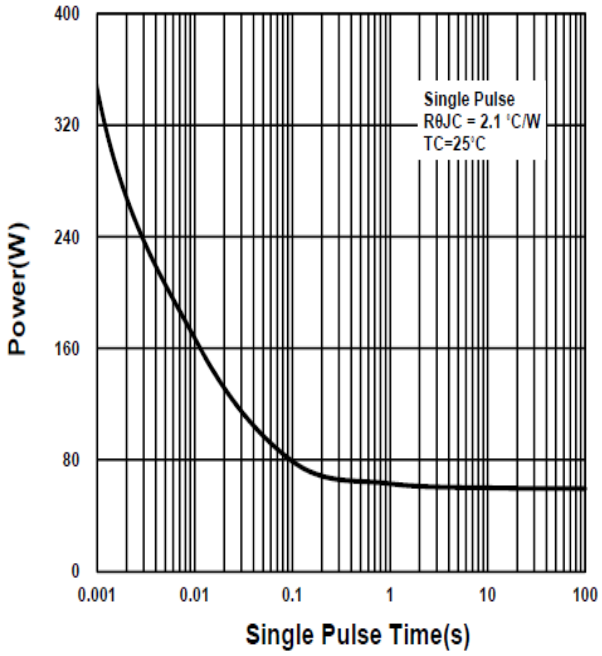
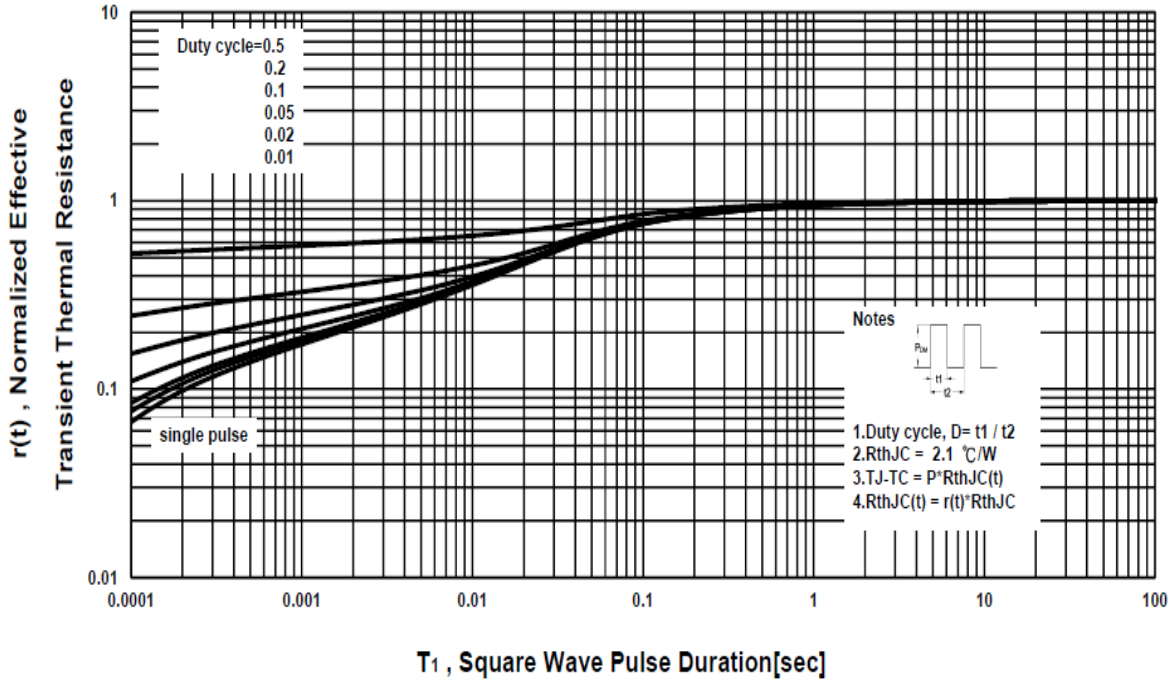
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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Package Dimension

TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	8.9	10	10.41	J	4.8		5.64
B	2.1	2.2	2.5	K	0.15		1.49
C	0.4	0.5	0.61	L	0.4	0.76	0.91
D	0.82	1.2	1.5	M	4.2	4.58	5
E	0.35	0.5	0.65	S	4.57	5.1	5.52
F	0		0.2	T	3.81	4.75	5.24
G	5.3	6.1	6.3	U	1.4		1.78
H	0.5		1.7	V	0.55	1.25	1.7
I	6.3	6.5	6.8